

# 74LVT244A; 74LVTH244A

3.3 V octal buffer/line driver; 3-state

Rev. 03 — 15 March 2006

Product data sheet

## 1. General description

The 74LVT244A; 74LVTH244A is a high-performance BiCMOS product designed for  $V_{CC}$  operation at 3.3 V.

This device is an octal buffer that is ideal for driving bus lines. The device features two output enables ( $1\overline{OE}$ ,  $2\overline{OE}$ ), each controlling four of the 3-state outputs.

## 2. Features

- Octal bus interface
- 3-state buffers
- Output capability: +64 mA and -32 mA
- TTL input and output switching levels
- Input and output interface capability to systems at 5 V supply
- Bus hold data inputs eliminate need for external pull-up resistors to hold unused inputs
- Power-up 3-state
- Live insertion and extraction permitted
- No bus current loading when output is tied to 5 V bus
- Latch-up protection:
  - ◆ JESD78: exceeds 500 mA
- ESD protection:
  - ◆ HBM EIA/JESD22-A114-C exceeds 2000 V
  - ◆ MM EIA/JESD22-A115-A 200 V

## 3. Quick reference data

Table 1. Quick reference data

$GND = 0 \text{ V}$ ;  $T_{amb} = 25^\circ\text{C}$ .

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{PLH}$	LOW-to-HIGH propagation delay nAn to nYn	$C_L = 50 \text{ pF}$ ; $V_{CC} = 3.3 \text{ V}$	-	2.5	-	ns
$t_{PHL}$	HIGH-to-LOW propagation delay nAn to nYn	$C_L = 50 \text{ pF}$ ; $V_{CC} = 3.3 \text{ V}$	-	2.6	-	ns
$C_i$	input capacitance	$V_I = 0 \text{ V}$ or $3.0 \text{ V}$	-	4	-	pF
$C_o$	output capacitance	outputs disabled; $V_O = 0 \text{ V}$ or $3.0 \text{ V}$	-	8	-	pF
$I_{CC}$	quiescent supply current	outputs disabled; $V_{CC} = 3.6 \text{ V}$ ; $I_O = 0 \text{ A}$ ; $V_I = GND$ or $V_{CC}$	-	0.13	-	mA

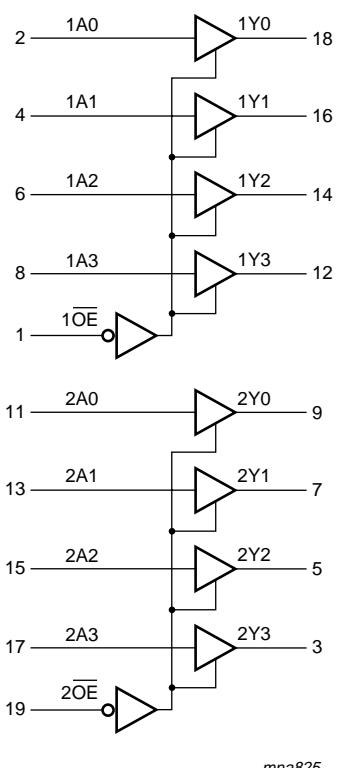
**PHILIPS**

## 4. Ordering information

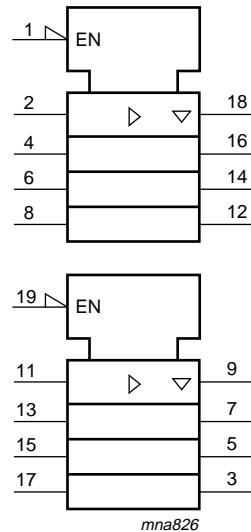
**Table 2. Ordering information**

Type number	Package			
	Temperature range	Name	Description	Version
74LVT244AD	-40 °C to +85 °C	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74LVT244ADB	-40 °C to +85 °C	SSOP20	plastic shrink small outline package; 20 leads; body width 5.3 mm	SOT339-1
74LVT244APW	-40 °C to +85 °C	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1
74LVTH244AD	-40 °C to +85 °C	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74LVTH244ADB	-40 °C to +85 °C	SSOP20	plastic shrink small outline package; 20 leads; body width 5.3 mm	SOT339-1
74LVTH244APW	-40 °C to +85 °C	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1

## 5. Functional diagram



**Fig 1. Logic symbol**



**Fig 2. IEC logic symbol**

## 6. Pinning information

### 6.1 Pinning

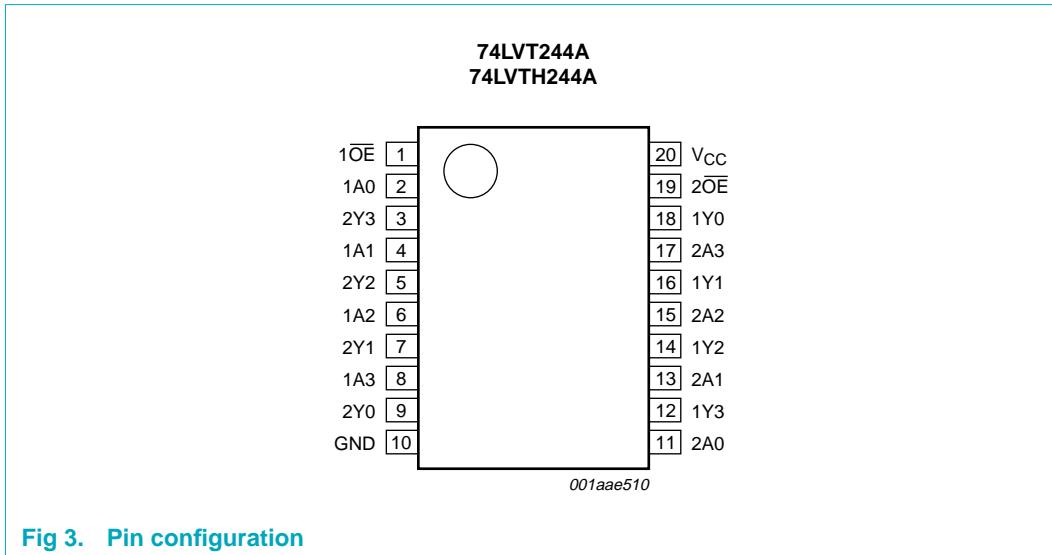


Fig 3. Pin configuration

### 6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
$\overline{OE}$	1	1 output enable input
1A0	2	1 data input 0
2Y3	3	2 data output 3
1A1	4	1 data input 1
2Y2	5	2 data output 2
1A2	6	1 data input 2
2Y1	7	2 data output 1
1A3	8	1 data input 3
2Y0	9	2 data output 0
GND	10	ground (0 V)
2A0	11	2 data input 0
1Y3	12	1 data output 3
2A1	13	2 data input 1
1Y2	14	1 data output 2
2A2	15	2 data input 2
1Y1	16	1 data output 1
2A3	17	2 data input 3
1Y0	18	1 data output 0
$\overline{OE}$	19	2 output enable input
$V_{CC}$	20	supply voltage

## 7. Functional description

### 7.1 Function table

**Table 4. Function table [1]**

Control	Input	Output
nOE	nAn	nYn
L	L	L
	H	H
H	X	Z

[1] H = HIGH voltage level;  
 L = LOW voltage level;  
 X = don't care;  
 Z = high-impedance OFF-state.

## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+4.6	V
V <sub>I</sub>	input voltage		[1] -0.5	+7.0	V
V <sub>O</sub>	output voltage	output in OFF-state or HIGH-state	[1] -0.5	+7.0	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < 0 V	-	-50	mA
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < 0 V	-	-50	mA
I <sub>O</sub>	output current	output in LOW-state	-	128	mA
		output in HIGH-state	-	-64	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		[2] -	150	°C

- [1] The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.  
 [2] The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability.

## 9. Recommended operating conditions

**Table 6. Operating conditions**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>CC</sub>	supply voltage		2.7	-	3.6	V
V <sub>I</sub>	input voltage		0	-	5.5	V
V <sub>IH</sub>	HIGH-state input voltage		2.0	-	-	V
V <sub>IL</sub>	LOW-state input voltage		-	-	0.8	V

**Table 6. Operating conditions ...continued**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I <sub>OH</sub>	HIGH-state output current		-	-	-32	mA
I <sub>OL</sub>	LOW-state output current	none	-	-	32	mA
		current duty cycle $\leq$ 50 %; $f_i \geq 1$ kHz	-	-	64	mA
T <sub>amb</sub>	ambient temperature	in free-air	-40	-	+85	°C
Δt/ΔV	input transition rise and fall rate	outputs enabled	-	-	10	ns/V

## 10. Static characteristics

**Table 7. Static characteristics**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>T<sub>amb</sub> = -40 °C to +85 °C [1]</b>						
V <sub>IK</sub>	input clamping voltage	V <sub>CC</sub> = 2.7 V; I <sub>IK</sub> = -18 mA	-	-0.9	-1.2	V
V <sub>OH</sub>	HIGH-state output voltage	V <sub>CC</sub> = 2.7 V to 3.6 V				
		I <sub>OH</sub> = -100 μA	V <sub>CC</sub> - 0.2	V <sub>CC</sub> - 0.1	-	V
		I <sub>OH</sub> = -8 mA	2.4	2.5	-	V
		V <sub>CC</sub> = 3.0 V				
V <sub>OL</sub>	LOW-state output voltage	I <sub>OH</sub> = -32 mA	2.0	2.2	-	V
		V <sub>CC</sub> = 2.7 V				
		I <sub>OL</sub> = 100 μA	-	0.1	0.2	V
		I <sub>OL</sub> = 24 mA	-	0.3	0.5	V
		V <sub>CC</sub> = 3.0 V				
		I <sub>OL</sub> = 16 mA	-	0.25	0.4	V
I <sub>LI</sub>	input leakage current	I <sub>OL</sub> = 32 mA	-	0.3	0.5	V
		I <sub>OL</sub> = 64 mA	-	0.4	0.55	V
		all input pins	-	0.1	10	μA
		control pins	V <sub>CC</sub> = 3.6 V; V <sub>I</sub> = V <sub>CC</sub> or GND	±0.1	±1	μA
I <sub>OFF</sub>	power-off leakage current	data pins	V <sub>CC</sub> = 3.6 V	[2]		
		V <sub>I</sub> = V <sub>CC</sub>	-	0.1	1	μA
		V <sub>I</sub> = 0 V	-	-1	-5	μA
		V <sub>CC</sub> = 0 V; V <sub>I</sub> or V <sub>O</sub> = 0 V to 4.5 V	-	1	±100	μA
I <sub>HOLD</sub>	bus hold current A input	V <sub>CC</sub> = 3 V	[3]			
		V <sub>I</sub> = 0.8 V	75	150	-	μA
		V <sub>I</sub> = 2.0 V	-75	-150	-	μA
		V <sub>CC</sub> = 0 V to 3.6 V				
I <sub>EX</sub>	external current into output	V <sub>I</sub> = 3.6 V	±500	-	-	μA
		output in HIGH-state when V <sub>O</sub> > V <sub>CC</sub> ; V <sub>O</sub> = 5.5 V; V <sub>CC</sub> = 3.0 V	-	60	125	μA

**Table 7. Static characteristics ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{O(\text{pu/pd})}$	power-up/power-down output current	$V_{CC} \leq 1.2 \text{ V}$ ; $V_O = 0.5 \text{ V}$ to $V_{CC}$ ; $V_I = \text{GND}$ or $V_{CC}$ ; $n\overline{OE}$ = don't care	[4] -	$\pm 1$	$\pm 100$	$\mu\text{A}$
$I_{OZ}$	OFF-state output current	$V_{CC} = 3.6 \text{ V}$ ; $V_I = V_{IH}$ or $V_{IL}$	-	1	5	$\mu\text{A}$
		output HIGH: $V_O = 3.0 \text{ V}$	-	-1	-5	$\mu\text{A}$
		output LOW: $V_O = 0.5 \text{ V}$	-	-	-	$\mu\text{A}$
$I_{CC}$	quiescent supply current	$V_{CC} = 3.6 \text{ V}$ ; $V_I = \text{GND}$ or $V_{CC}$ ;	-	-	-	-
		$I_O = 0 \text{ A}$	-	0.13	0.19	$\text{mA}$
		output HIGH	-	3	12	$\text{mA}$
		outputs disabled	[5] -	0.13	0.19	$\text{mA}$
$\Delta I_{CC}$	additional quiescent supply current	per input pin; $V_{CC} = 3.0 \text{ V}$ to $3.6 \text{ V}$ ; one input at $V_{CC} - 0.6 \text{ V}$ and other inputs at $V_{CC}$ or GND	[6] -	0.1	0.2	$\text{mA}$
$C_i$	input capacitance	$V_I = 0 \text{ V}$ or $3.0 \text{ V}$	-	4	-	$\text{pF}$
$C_o$	output capacitance	outputs disabled; $V_O = 0 \text{ V}$ or $3.0 \text{ V}$	-	8	-	$\text{pF}$

[1] All typical values are at  $T_{amb} = 25^\circ\text{C}$ .[2] Unused pins at  $V_{CC}$  or GND.

[3] This is the bus hold overdrive current required to force the input to the opposite logic state.

[4] This parameter is valid for any  $V_{CC}$  between 0 V and 1.2 V with a transition time of up to 10 ms. From  $V_{CC} = 1.2 \text{ V}$  to  $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$  a transition time of 100  $\mu\text{s}$  is permitted. This parameter is valid for  $T_{amb} = 25^\circ\text{C}$  only.[5]  $I_{CC}$  is measured with outputs pulled to  $V_{CC}$  or GND.[6] This is the increase in supply current for each input at the specified voltage level other than  $V_{CC}$  or GND.

## 11. Dynamic characteristics

**Table 8. Dynamic characteristics**Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 6](#).

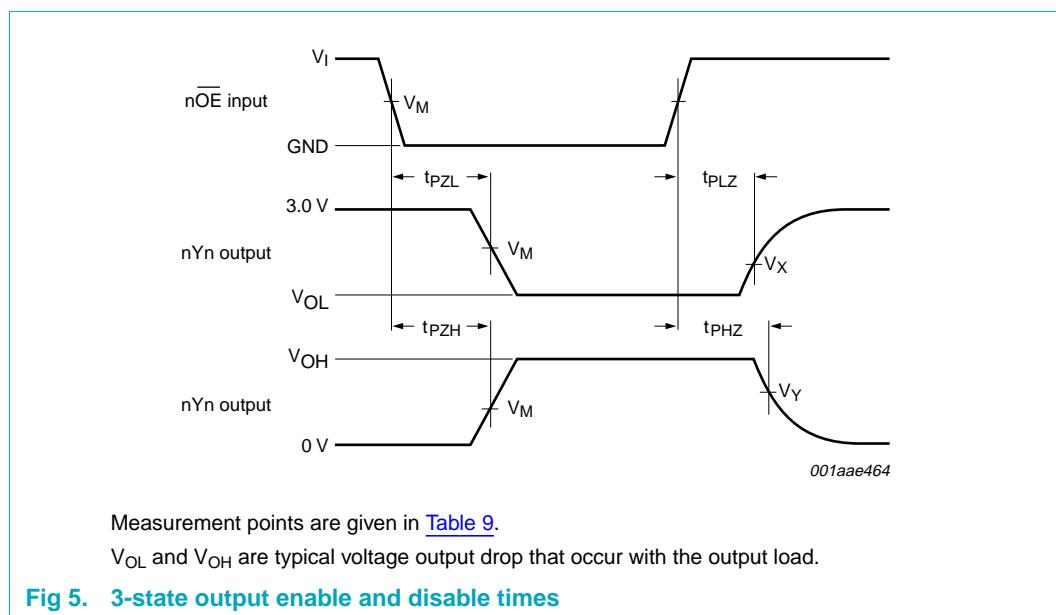
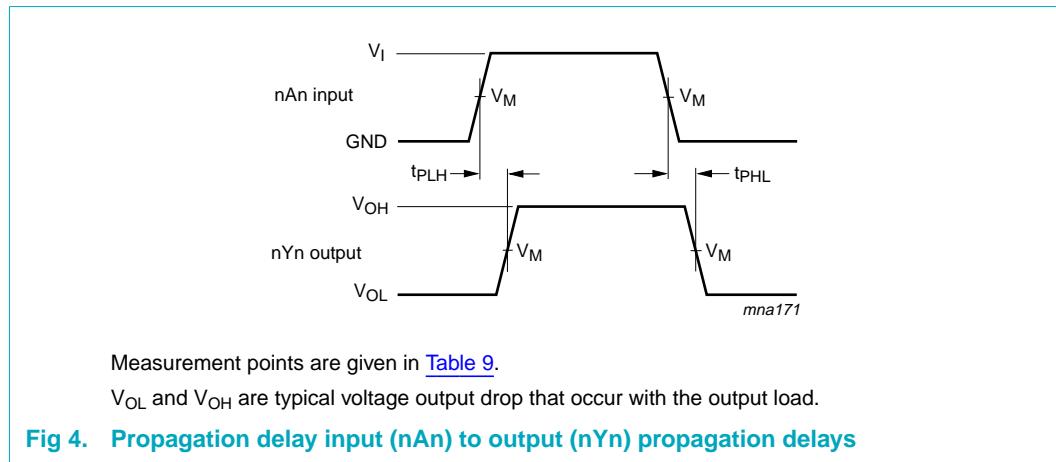
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$T_{amb} = -40^\circ\text{C}$ to $+85^\circ\text{C}$ [1]						
$t_{PLH}$	LOW-to-HIGH propagation delay nAn to nYn	see <a href="#">Figure 4</a>	-	-	5.0	ns
		$V_{CC} = 2.7 \text{ V}$	-	-	5.0	ns
		$V_{CC} = 3.0 \text{ V}$ to $3.6 \text{ V}$	1	2.5	4.1	ns
$t_{PHL}$	HIGH-to-LOW propagation delay nAn to nYn	see <a href="#">Figure 4</a>	-	-	5.1	ns
		$V_{CC} = 2.7 \text{ V}$	-	-	5.1	ns
		$V_{CC} = 3.0 \text{ V}$ to $3.6 \text{ V}$	1	2.6	4.1	ns
$t_{PZH}$	output enable time to HIGH-level	see <a href="#">Figure 5</a>	-	-	6.3	ns
		$V_{CC} = 2.7 \text{ V}$	-	-	6.3	ns
		$V_{CC} = 3.0 \text{ V}$ to $3.6 \text{ V}$	1	3.2	5.2	ns
$t_{PZL}$	output enable time to LOW-level	see <a href="#">Figure 5</a>	-	-	6.7	ns
		$V_{CC} = 2.7 \text{ V}$	-	-	6.7	ns
		$V_{CC} = 3.0 \text{ V}$ to $3.6 \text{ V}$	1.1	3.1	5.2	ns

**Table 8. Dynamic characteristics ...continued**Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 6](#).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{PHZ}$	output disable time from HIGH-level	see <a href="#">Figure 5</a>				
		$V_{CC} = 2.7 \text{ V}$	-	-	6.3	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.9	3.3	5.6	ns
$t_{PLZ}$	output disable time from LOW-level	see <a href="#">Figure 5</a>				
		$V_{CC} = 2.7 \text{ V}$	-	-	5.6	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.8	3.3	5.1	ns

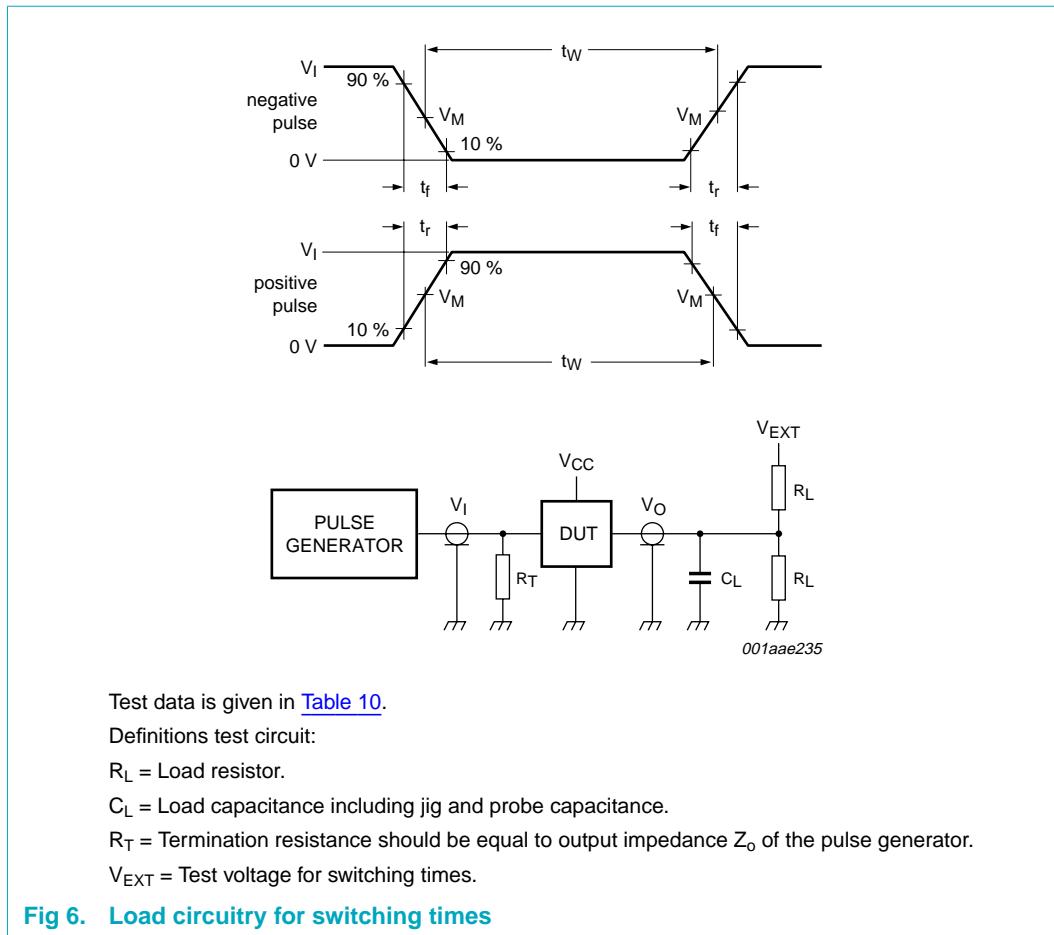
[1] All typical values are at  $V_{CC} = 3.3 \text{ V}$  and  $T_{amb} = 25^\circ\text{C}$ .

## 12. Waveforms



**Table 9. Measurement points**

Input	Output		
$V_M$	$V_M$	$V_X$	$V_Y$
1.5 V	1.5 V	$V_{OL} + 0.3 \text{ V}$	$V_{OH} - 0.3 \text{ V}$

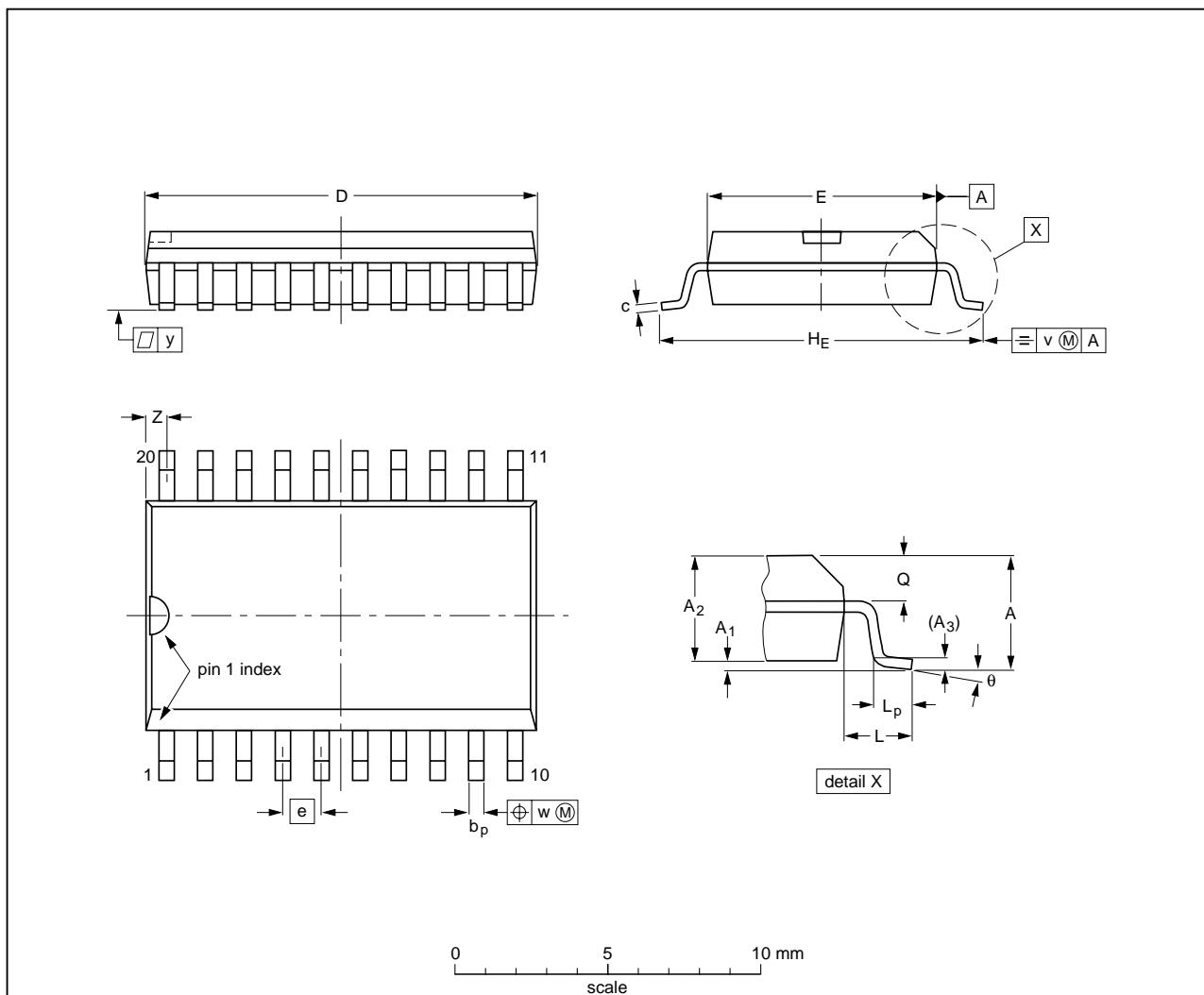
**Table 10. Test data**

Input				Load		$V_{EXT}$		
$V_I$	$f_i$	$t_W$	$t_r, t_f$	$C_L$	$R_L$	$t_{PHZ}, t_{PZH}$	$t_{PLZ}, t_{PZL}$	$t_{PLH}, t_{PHL}$
2.7 V	$\leq 10$ MHz	500 ns	$\leq 2.5$ ns	50 pF	500 $\Omega$	GND	6 V	open

## 13. Package outline

SO20: plastic small outline package; 20 leads; body width 7.5 mm

SOT163-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	b <sub>p</sub>	c	D <sup>(1)</sup>	E <sup>(1)</sup>	e	H <sub>E</sub>	L	L <sub>p</sub>	Q	v	w	y	z <sup>(1)</sup>	θ
mm	2.65 0.1	0.3 2.25	2.45 0.25	0.25	0.49 0.36	0.32 0.23	13.0 12.6	7.6 7.4	1.27	10.65 10.00	1.4	1.1 0.4	1.1 1.0	0.25	0.25	0.1	0.9 0.4	8° 0°
inches	0.1	0.012 0.004	0.096 0.089	0.01	0.019 0.014	0.013 0.009	0.51 0.49	0.30 0.29	0.05	0.419 0.394	0.055	0.043 0.016	0.043 0.039	0.01	0.01	0.004	0.035 0.016	

Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT163-1	075E04	MS-013			-99-12-27 03-02-19

Fig 7. Package outline SOT163-1 (SO20)

SSOP20: plastic shrink small outline package; 20 leads; body width 5.3 mm

SOT339-1

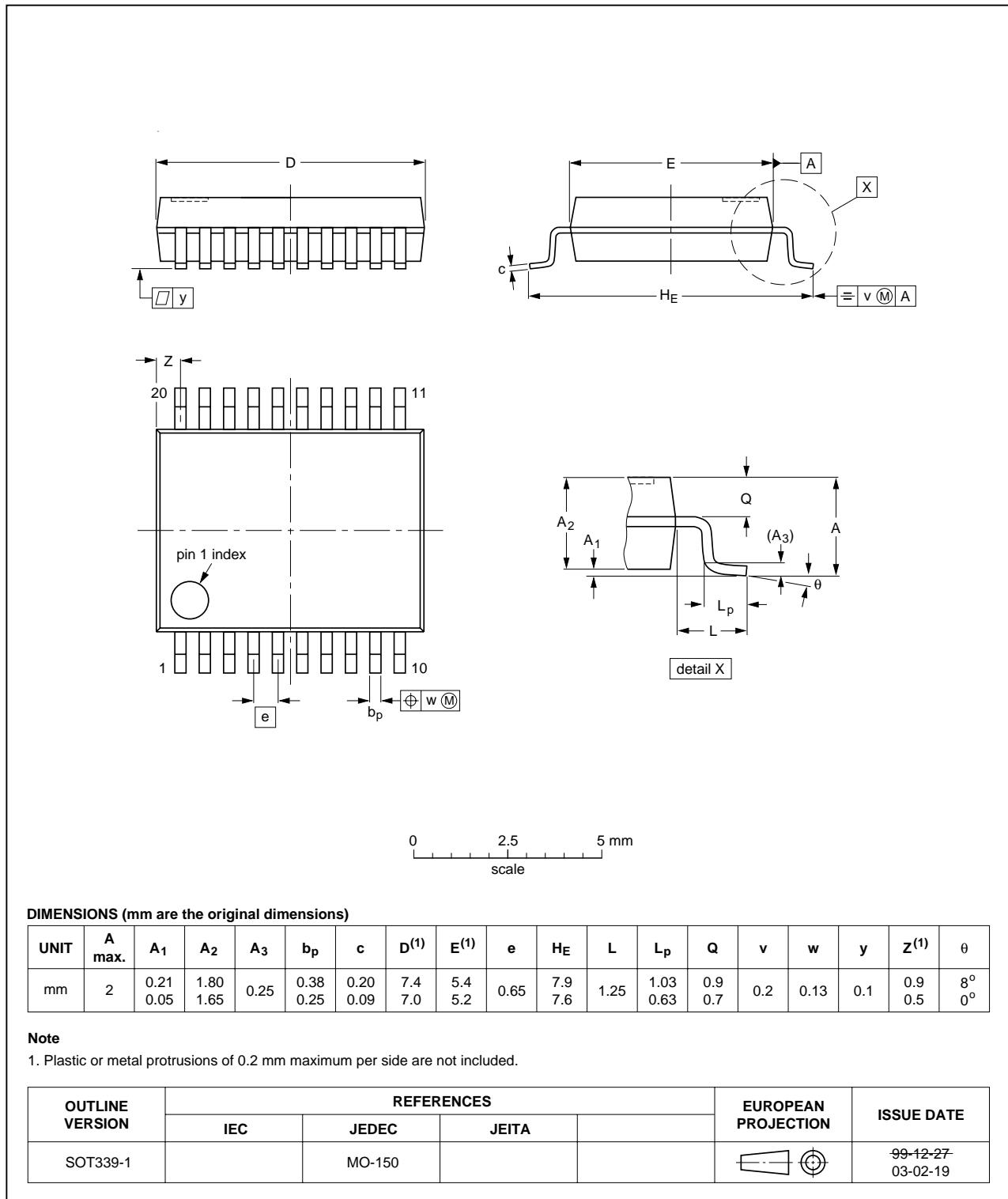


Fig 8. Package outline SOT339-1 (SSOP20)

TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm

SOT360-1

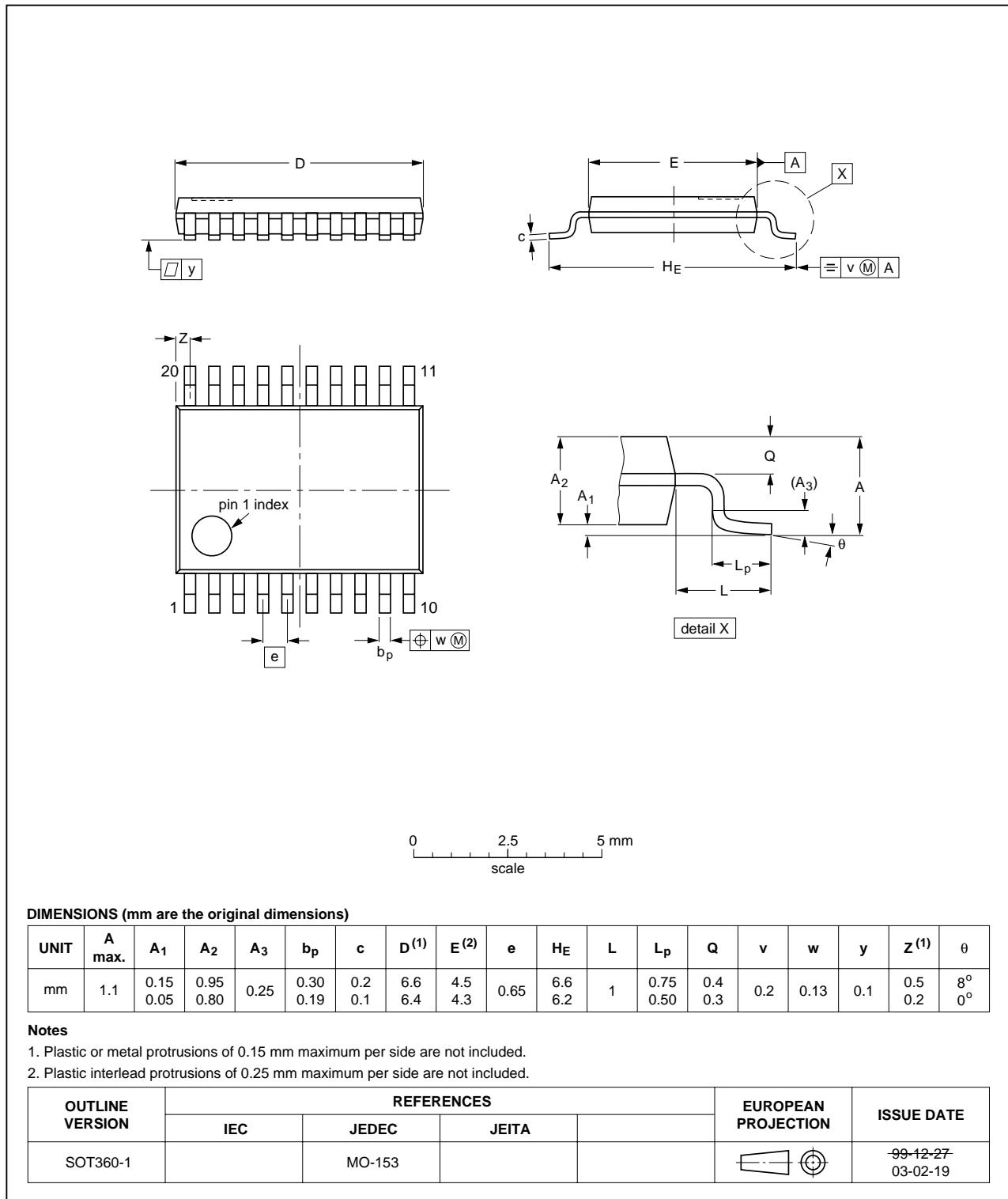


Fig 9. Package outline SOT360-1 (TSSOP20)

## 14. Abbreviations

**Table 11. Abbreviations**

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

## 15. Revision history

**Table 12. Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVT_LVTH244A_3	20060315	Product data sheet	-	74LVT244A_2
Modifications:	<ul style="list-style-type: none"> <li>The format of this data sheet has been redesigned to comply with the new presentation and information standard of Philips Semiconductors.</li> <li><u>Section 4:</u> added type numbers 74LVTH244AD, 74LVTH244ADB and 74LVTH244APW.</li> </ul>			
74LVT244A_2	19980219	Product specification	-	74LVT244A_1
74LVT244A_1	19951114	Product specification	-	-

## 16. Legal information

### 16.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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